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ABSTRACT

The substrate processing apparatus according to the present invention is aimed to stably
5 and efficiently perform a deposition process on a substrate W. The substrate processing apparatus supports the substrate W in a position facing a heater portion and thus rotates a holding member holding the substrate W. Furthermore, the heating
10 portion houses a SiC heater and a heat reflecting member in an internal portion of a quartz bell jar made of transparent quartz, and depressurizes an internal space of a processing vessel and an internal space of the quartz bell jar at the same time;
15 thereby allowing the thickness of the quartz bell jar to be thinner, and thus improving thermal conductivity of heat from the SiC heater and preventing contamination by the SiC heater.